



ELECTRONICS, INC.
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NTE2528 (NPN) & NTE2529 (PNP) Silicon Complementary Transistors High Voltage Switch TO251

Features:

- High Voltage and High Current Capacity
- Fast Switching Time
- TO251 Type Package

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector Base Voltage, V_{CBO}	180V
Collector Emitter Voltage, V_{CEO}	160V
Emitter Base Voltage, V_{EBO}	6V
Collector Current, I_C	
Continuous	1.5A
Pulse	2.5A
Collector Power Dissipation, P_C	
$T_A = +25^\circ\text{C}$	1W
$T_C = +25^\circ\text{C}$	15W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

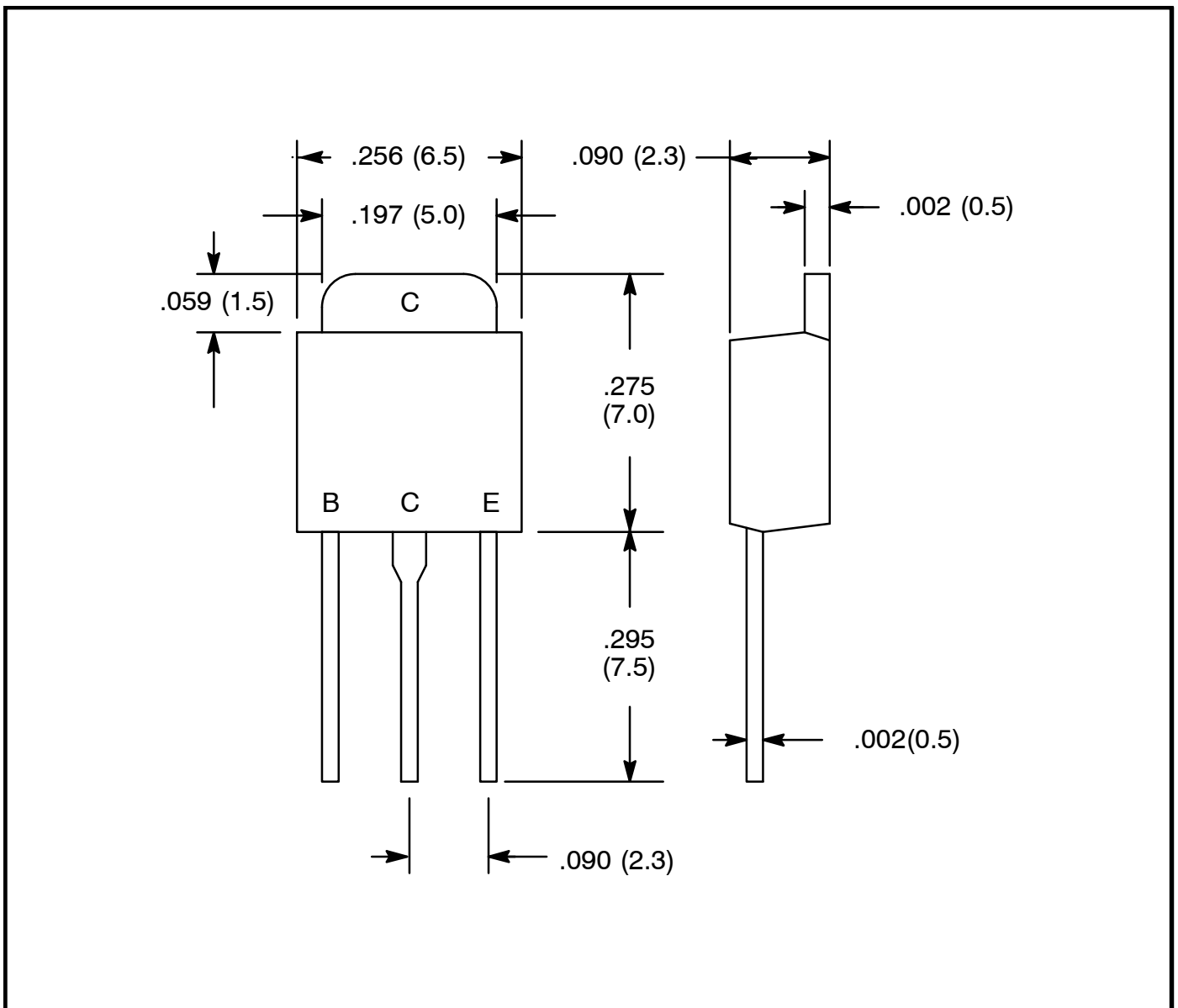
Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 120V, I_E = 0$	-	-	1.0	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4V, I_C = 0$	-	-	1.0	μA
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 100\text{mA}$	100	-	400	
		$V_{CE} = 5V, I_C = 10A$	80	-	-	
Gain-Bandwidth Product	f_T	$V_{CE} = 10V, I_C = 50\text{mA}$	-	120	-	MHz
Output Capacitance	C_{ob}	$V_{CB} = 10V, f = 1\text{MHz}$	-	12	-	pF
NTE2528			-	22	-	pF
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$	-	0.13	0.5	V
NTE2528			-	0.2	0.45	V
NTE2529						

Electrical Characteristics (Cont'd): ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$	-	0.85	1.2	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	180	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, R_{BE} = \infty$	160	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	6	-	-	V
Turn-On Time	t_{on}	$V_{CC} = 100\text{V}, V_{BE} = -5\text{V},$ $10I_{B1} = -10I_{B2} = I_C = 700\text{mA},$ Pulse Width = $20\mu\text{s},$ Duty Cycle $\leq 1\%$, Note 1	-	60	-	ns
Storage Time NTE2528	t_{stg}		-	1.2	-	ns
NTE2529			-	0.7	-	ns
Fall Time NTE2528	t_f		-	80	-	ns
NTE2529			-	50	-	ns

Note 1. For NTE2529, the polarity is reversed.



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